

Appl. No. 10/063,822  
Amdt. Dated January 21, 2005  
Reply to Office action of October 21, 2004

# AMENDMENTS TO THE SPECIFICATION

In paragraph [0014]:

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In addition, in other embodiments of the present invention, the multiple-quantum well structure for the InGaN light-emitting layer 14 can be replaced with a single-quantum well structure. The GaN buffer layer 11 and/or the p-type contact layer 16 can be optional to be removed from the LED structure. ~~The n<sup>+</sup>-type GaN materials can be replaced with n-type GaN materials.~~ The n<sup>+</sup>-type GaN contact layer 12 can be replaced by an n-type GaN layer.

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